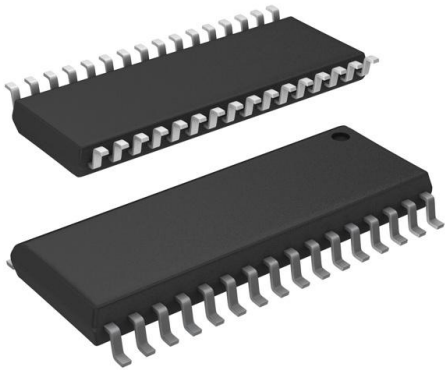


# CY62148EV30LL-55ZSXE Datasheet

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DiGi Electronics Part Number	CY62148EV30LL-55ZSXE-DG
Manufacturer	<a href="#">Infineon Technologies</a>
Manufacturer Product Number	CY62148EV30LL-55ZSXE
Description	IC SRAM 4MBIT PARALLEL 32SOIC
Detailed Description	SRAM - Asynchronous Memory IC 4Mbit Parallel 55 ns 32-SOIC

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## Purchase and inquiry

Manufacturer Product Number:

CY62148EV30LL-55ZSXE

Series:

MoBL®

DiGi-Electronics Programmable:

Not Verified

Memory Format:

SRAM

Memory Size:

4Mbit

Memory Interface:

Parallel

Access Time:

55 ns

Operating Temperature:

-40°C ~ 125°C (TA)

Package / Case:

32-SOIC (0.445", 11.30mm Width)

Base Product Number:

CY62148

Manufacturer:

Infineon Technologies

Product Status:

Obsolete

Memory Type:

Volatile

Technology:

SRAM - Asynchronous

Memory Organization:

512K x 8

Write Cycle Time - Word, Page:

55ns

Voltage - Supply:

2.2V ~ 3.6V

Mounting Type:

Surface Mount

Supplier Device Package:

32-SOIC

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8542.32.0041

Moisture Sensitivity Level (MSL):

3 (168 Hours)

ECCN:

3A991B2A



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**Continuity of document content**

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**Continuity of ordering part numbers**

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CY62148EV30 MoBL

## 4-Mbit (512K × 8) Static RAM

## Features

- Very high speed: 45 ns
  - Wide voltage range: 2.20 V to 3.60 V
- Temperature range:
  - Industrial: -40 °C to +85 °C
  - Automotive-A: -40 °C to +85 °C
- Pin compatible with CY62148DV30
- Ultra low standby power
  - Typical standby current: 2.5 μA
  - Maximum standby current: 7 μA (Industrial)
- Ultra low active power
  - Typical active current: 3.5 mA at f = 1 MHz
- Easy memory expansion with  $\overline{CE}$  and  $\overline{OE}$  features
- Automatic power down when deselected
- Complementary metal oxide semiconductor (CMOS) for optimum speed and power
- Available in Pb-free 36-ball very fine-pitch ball grid array (VFBGA), 32-pin thin small outline package (TSOP) II, and 32-pin small outline integrated circuit (SOIC)<sup>[1]</sup> packages

## Functional Description

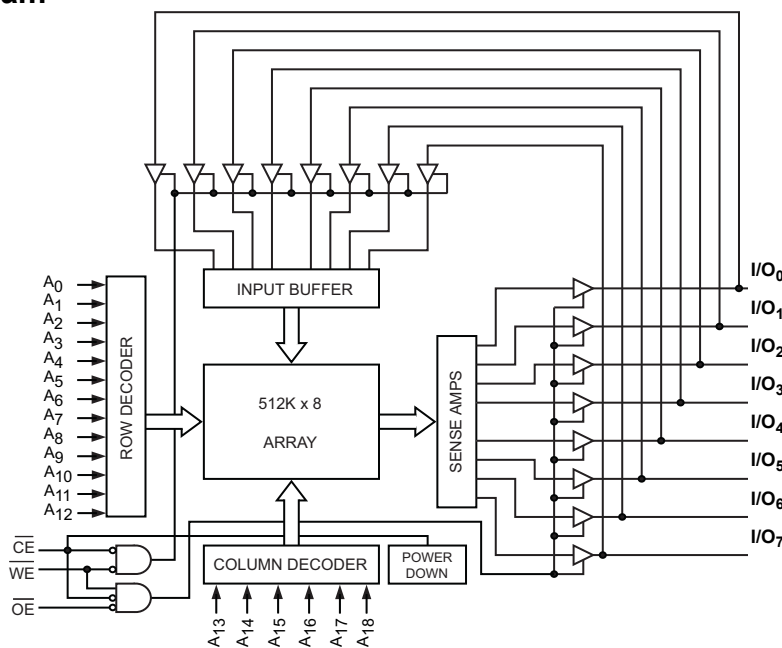
The CY62148EV30 is a high performance CMOS static RAM organized as 512K words by 8 bits. This device features advanced circuit design to provide ultra low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power down feature that significantly reduces power consumption. Placing the device into standby mode reduces power consumption by more than 99 percent when deselected ( $\overline{CE}$  HIGH). The eight input and output pins (I/O<sub>0</sub> through I/O<sub>7</sub>) are placed in a high impedance state when the device is deselected ( $\overline{CE}$  HIGH), the outputs are disabled ( $\overline{OE}$  HIGH), or during a write operation ( $\overline{CE}$  LOW and  $\overline{WE}$  LOW).

To write to the device, take Chip Enable ( $\overline{CE}$ ) and Write Enable ( $\overline{WE}$ ) inputs LOW. Data on the eight I/O pins (I/O<sub>0</sub> through I/O<sub>7</sub>) is then written into the location specified on the address pins (A<sub>0</sub> through A<sub>18</sub>).

To read from the device, take Chip Enable ( $\overline{CE}$ ) and Output Enable ( $\overline{OE}$ ) LOW while forcing Write Enable ( $\overline{WE}$ ) HIGH. Under these conditions, the contents of the memory location specified by the address pins appear on the I/O pins.

For a complete list of related 1documentation, [click here](#).

## Logic Block Diagram



## Note

1. SOIC package is available only in 55 ns speed bin.



## Contents

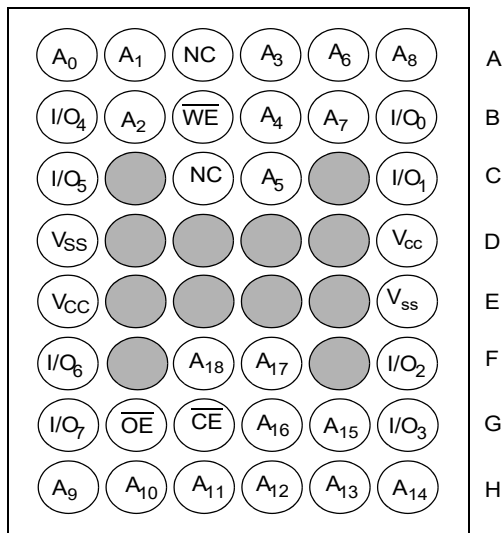
<b>Pin Configurations</b> .....	<b>3</b>	<b>Ordering Information</b> .....	<b>11</b>
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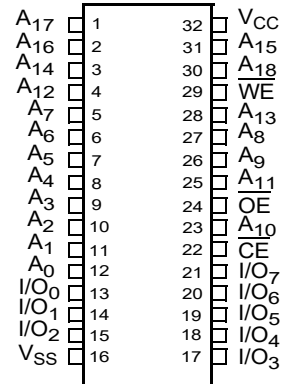
## Pin Configurations

VFPGA, SOIC and TSOP II pinouts are as follows. [2, 3]

**36-ball VFPGA pinout**  
Top View



**32-pin SOIC/TSOP II pinout**  
Top View



## Product Portfolio

Product	Range	V <sub>CC</sub> Range (V)	Speed (ns)	Power Dissipation								
				Operating I <sub>CC</sub> (mA)				Standby I <sub>SB2</sub> (μA)				
				f = 1 MHz		f = f <sub>max</sub>						
Min	Typ <sup>[4]</sup>	Max	Typ <sup>[4]</sup>	Max	Typ <sup>[4]</sup>	Max	Typ <sup>[4]</sup>	Max				
CY62148EV30LL	VFPGA	Industrial	45	2.2	3.0	3.6	3.5	6	15	20	2.5	7
	TSOP II	Industrial / Automotive-A										
	SOIC	Industrial	55	2.2	3.0	3.6	3.5	6	15	20	2.5	7

### Notes

- SOIC package is available only in 55 ns speed bin.
- NC pins are not connected on the die.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = V<sub>CC(typ)</sub>, T<sub>A</sub> = 25 °C.



## Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature ..... -65 °C to +150 °C

Ambient temperature  
with power applied ..... 55 °C to +125 °C

Supply voltage  
to ground potential ..... -0.3 V to  $V_{CC(max)}$  + 0.3 V

DC voltage applied to outputs  
in High Z State <sup>[5, 6]</sup> ..... -0.3 V to  $V_{CC(max)}$  + 0.3 V

DC input voltage <sup>[5, 6]</sup> ..... -0.3 V to  $V_{CC(max)}$  + 0.3 V

Output current into outputs (LOW) ..... 20 mA

Static discharge voltage  
(MIL-STD-883, Method 3015) ..... > 2001 V

Latch up current ..... > 200 mA

## Operating Range

Product	Range	Ambient Temperature	$V_{CC}$ <sup>[7]</sup>
CY62148EV30	Industrial/ Automotive-A	-40 °C to +85 °C	2.2 V to 3.6 V

## Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions	-45 (Industrial / Automotive-A)			-55 <sup>[8]</sup>			Unit
			Min	Typ <sup>[9]</sup>	Max	Min	Typ <sup>[9]</sup>	Max	
$V_{OH}$	Output high voltage	$I_{OH} = -0.1$ mA	2.0	–	–	2.0	–	–	V
		$I_{OH} = -1.0$ mA, $V_{CC} \geq 2.70$ V	2.4	–	–	2.4	–	–	V
$V_{OL}$	Output low voltage	$I_{OL} = 0.1$ mA	–	–	0.4	–	–	0.2	V
		$I_{OL} = 2.1$ mA, $V_{CC} \geq 2.70$ V	–	–	0.4	–	–	0.4	V
$V_{IH}$	Input high voltage	$V_{CC} = 2.2$ V to 2.7 V	1.8	–	$V_{CC} + 0.3$	1.8	–	$V_{CC} + 0.3$	V
		$V_{CC} = 2.7$ V to 3.6 V	2.2	–	$V_{CC} + 0.3$	2.2	–	$V_{CC} + 0.3$	V
$V_{IL}$	Input low voltage	$V_{CC} = 2.2$ V to 2.7 V	For VFBGA and TSOP II packages	-0.3	–	0.6	–	–	V
			For SOIC package	–	–	–	-0.3	–	0.4 <sup>[10]</sup>
		$V_{CC} = 2.7$ V to 3.6 V	For VFBGA and TSOP II packages	-0.3	–	0.8	–	–	V
			For SOIC package	–	–	–	-0.3	–	0.6 <sup>[10]</sup>
$I_{IX}$	Input leakage current	$GND \leq V_I \leq V_C$	-1	–	+1	-1	–	+1	$\mu$ A
$I_{OZ}$	Output leakage current	$GND \leq V_O \leq V_{CC}$ , Output disabled	-1	–	+1	-1	–	+1	$\mu$ A
$I_{CC}$	$V_{CC}$ operating supply current	$f = f_{max} = 1/t_{RC}$	–	15	20	–	15	20	mA
		$f = 1$ MHz		3.5	6		3.5	6	
$I_{SB1}$ <sup>[11]</sup>	Automatic CE power down current – CMOS inputs	$\overline{CE} \geq V_{CC} - 0.2$ V, $V_{IN} \geq V_{CC} - 0.2$ V, $V_{IN} \leq 0.2$ V, $f = f_{max}$ (Address and Data Only), $f = 0$ (OE and WE), $V_{CC} = 3.60$ V	–	2.5	7	–	2.5	7	$\mu$ A
$I_{SB2}$ <sup>[11]</sup>	Automatic CE power down current – CMOS inputs	$\overline{CE} \geq V_{CC} - 0.2$ V, $V_{IN} \geq V_{CC} - 0.2$ V or $V_{IN} \leq 0.2$ V, $f = 0$ , $V_{CC} = 3.60$ V	–	2.5	7	–	2.5	7	$\mu$ A

### Notes

- $V_{IL(min)}$  = -2.0 V for pulse durations less than 20 ns.
- $V_{IH(max)}$  =  $V_{CC} + 0.75$  V for pulse durations less than 20 ns.
- Full device AC operation assumes a minimum of 100  $\mu$ s ramp time from 0 to  $V_{CC(min)}$  and 200  $\mu$ s wait time after  $V_{CC}$  stabilization.
- SOIC package is available only in 55 ns speed bin.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at  $V_{CC} = V_{CC(typ)}$ ,  $T_A = 25$  °C.
- Under DC conditions the device meets a  $V_{IL}$  of 0.8V (for  $V_{CC}$  range of 2.7 V to 3.6 V) and 0.6 V (for  $V_{CC}$  range of 2.2 V to 2.7 V). However, in dynamic conditions Input LOW voltage applied to the device must not be higher than 0.6V and 0.4V for the above ranges. This is applicable to SOIC package only.
- Chip Enable (CE) must be HIGH at CMOS level to meet the  $I_{SB1}$  /  $I_{SB2}$  /  $I_{CCDR}$  spec. Other inputs can be left floating.

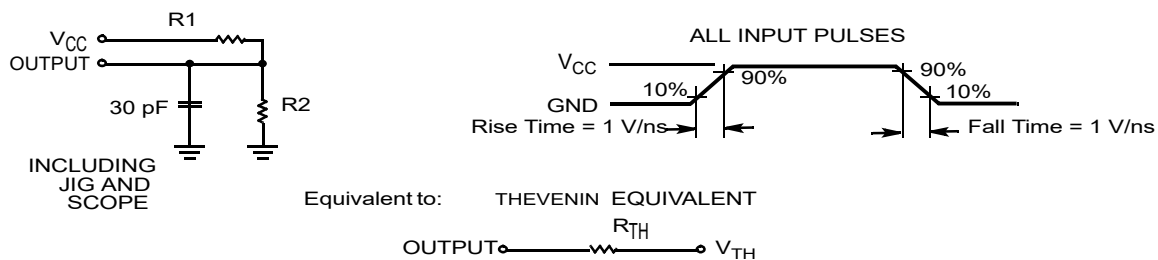
## Capacitance

Parameter <sup>[12]</sup>	Description	Test Conditions	Max	Unit
$C_{IN}$	Input capacitance	$T_A = 25\text{ }^\circ\text{C}$ , $f = 1\text{ MHz}$ , $V_{CC} = V_{CC(\text{typ})}$	10	pF
$C_{OUT}$	Output capacitance		10	pF

## Thermal Resistance

Parameter <sup>[12]</sup>	Description	Test Conditions	36-ball VFBGA Package	32-pin TSOP II Package	32-pin SOIC Package	Unit
$\Theta_{JA}$	Thermal resistance (junction to ambient)	Still air, soldered on a $3 \times 4.5$ inch, four-layer printed circuit board	44.79	59.10	51.57	$^\circ\text{C/W}$
$\Theta_{JC}$	Thermal resistance (junction to case)		23.17	12.19	25.01	$^\circ\text{C/W}$

## AC Test Loads and Waveforms

**Figure 1. AC Test Loads and Waveforms**

Parameter	2.50 V	3.0 V	Unit
$R_1$	16667	1103	$\Omega$
$R_2$	15385	1554	$\Omega$
$R_{TH}$	8000	645	$\Omega$
$V_{TH}$	1.20	1.75	V

**Note**

12. Tested initially and after any design or process changes that may affect these parameters.

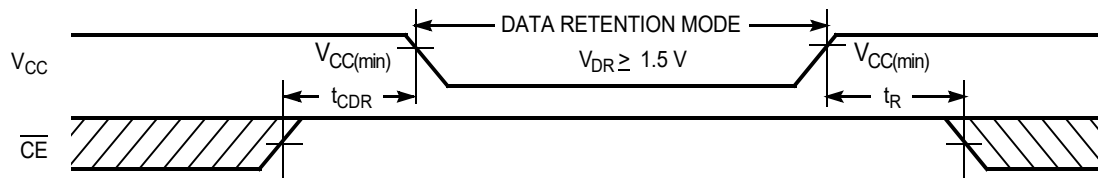
## Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Min	Typ <sup>[13]</sup>	Max	Unit
$V_{DR}$	$V_{CC}$ for data retention		1.5	–	–	V
$I_{CCDR}$ <sup>[14]</sup>	Data retention current	$V_{CC} = 1.5\text{ V}$ , $\overline{CE} \geq V_{CC} - 0.2\text{ V}$ , $V_{IN} \geq V_{CC} - 0.2\text{ V}$ or $V_{IN} \leq 0.2\text{ V}$	–	3	8.8	$\mu\text{A}$
$t_{CDR}$ <sup>[15]</sup>	Chip deselect to data retention time		0	–	–	ns
$t_R$ <sup>[16]</sup>	Operation recovery time	CY62148EV30LL-45	45	–	–	ns
		CY62148EV30LL-55	55	–	–	ns

## Data Retention Waveform

Figure 2. Data Retention Waveform



### Notes

13. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at  $V_{CC} = V_{CC(typ)}$ ,  $T_A = 25\text{ }^\circ\text{C}$ .
14. Chip Enable ( $\overline{CE}$ ) must be HIGH at CMOS level to meet the  $I_{SB1} / I_{SB2} / I_{CCDR}$  spec. Other inputs can be left floating.
15. Tested initially and after any design or process changes that may affect these parameters.
16. Full device AC operation requires linear  $V_{CC}$  ramp from  $V_{DR}$  to  $V_{CC(min)} \geq 100\text{ }\mu\text{s}$  or stable at  $V_{CC(min)} \geq 100\text{ }\mu\text{s}$ .



## Switching Characteristics

Over the Operating Range

Parameter <sup>[17, 18]</sup>	Description	-45 (Industrial / Automotive-A)		-55 <sup>[19]</sup>		Unit
		Min	Max	Min	Max	
<b>Read Cycle</b>						
t <sub>RC</sub>	Read cycle time	45	–	55	–	ns
t <sub>AA</sub>	Address to data valid	–	45	–	55	ns
t <sub>OHA</sub>	Data hold from address change	10	–	10	–	ns
t <sub>ACE</sub>	$\overline{CE}$ LOW to data valid	–	45	–	55	ns
t <sub>DOE</sub>	$\overline{OE}$ LOW to data valid	–	22	–	25	ns
t <sub>LZOE</sub>	$\overline{OE}$ LOW to Low Z <sup>[20]</sup>	5	–	5	–	ns
t <sub>HZOE</sub>	$\overline{OE}$ HIGH to High Z <sup>[20, 21]</sup>	–	18	–	20	ns
t <sub>LZCE</sub>	$\overline{CE}$ LOW to Low Z <sup>[20]</sup>	10	–	10	–	ns
t <sub>HZCE</sub>	$\overline{CE}$ HIGH to High Z <sup>[20, 21]</sup>	–	18	–	20	ns
t <sub>PU</sub>	$\overline{CE}$ LOW to power-up	0	–	0	–	ns
t <sub>PD</sub>	$\overline{CE}$ HIGH to power-down	–	45	–	55	ns
<b>Write Cycle <sup>[22, 23]</sup></b>						
t <sub>WC</sub>	Write cycle time	45	–	55	–	ns
t <sub>SCE</sub>	$\overline{CE}$ LOW to write end	35	–	40	–	ns
t <sub>AW</sub>	Address setup to write end	35	–	40	–	ns
t <sub>HA</sub>	Address hold from write end	0	–	0	–	ns
t <sub>SA</sub>	Address setup to write start	0	–	0	–	ns
t <sub>PWE</sub>	$\overline{WE}$ pulse width	35	–	40	–	ns
t <sub>SD</sub>	Data setup to write end	25	–	25	–	ns
t <sub>HD</sub>	Data hold from write end	0	–	0	–	ns
t <sub>HZWE</sub>	$\overline{WE}$ LOW to High Z <sup>[20, 21]</sup>	–	18	–	20	ns
t <sub>LZWE</sub>	$\overline{WE}$ HIGH to Low Z <sup>[20]</sup>	10	–	10	–	ns

### Notes

17. In an earlier revision of this device, under a specific application condition, READ and WRITE operations were limited to switching of the chip enable signal as described in the Application Note AN66311. However, the issue has been fixed and in production now, and hence, this Application Note is no longer applicable. It is available for download on our website as it contains information on the date code of the parts, beyond which the fix has been in production.
18. Test Conditions for all parameters other than tri-state parameters assume signal transition time of 3 ns or less (1 V/ns), timing reference levels of  $V_{CC(typ)}/2$ , input pulse levels of 0 to  $V_{CC(typ)}$ , and output loading of the specified  $I_{OL}/I_{OH}$  as shown in the Figure 1 on page 5.
19. SOIC package is available only in 55 ns speed bin.
20. At any given temperature and voltage condition, t<sub>HZCE</sub> is less than t<sub>LZCE</sub>, t<sub>HZOE</sub> is less than t<sub>LZOE</sub>, and t<sub>HZWE</sub> is less than t<sub>LZWE</sub> for any given device.
21. t<sub>HZOE</sub>, t<sub>HZCE</sub>, and t<sub>HZWE</sub> transitions are measured when the output enter a high impedance state.
22. The internal write time of the memory is defined by the overlap of  $\overline{WE}$ ,  $\overline{CE} = V_{IL}$ . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must be referenced to the edge of the signal that terminates the write.
23. The minimum write cycle pulse width for Write Cycle No. 3 ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW) should be equal to the sum of t<sub>SD</sub> and t<sub>HZWE</sub>.

## Switching Waveforms

Figure 3. Read Cycle No. 1 (Address Transition Controlled) [24, 25]

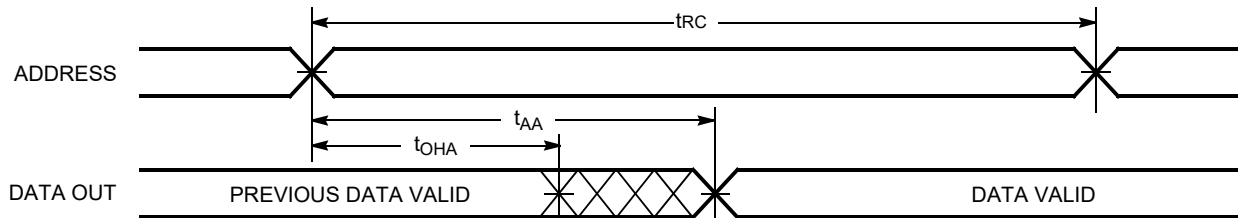


Figure 4. Read Cycle No. 2 ( $\overline{\text{OE}}$  Controlled) [25, 26]

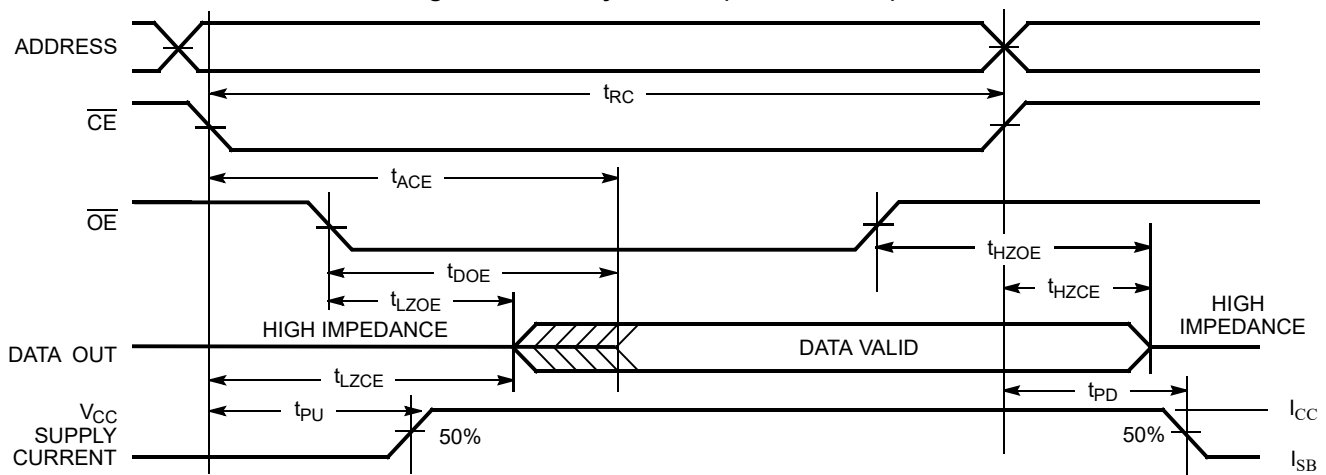
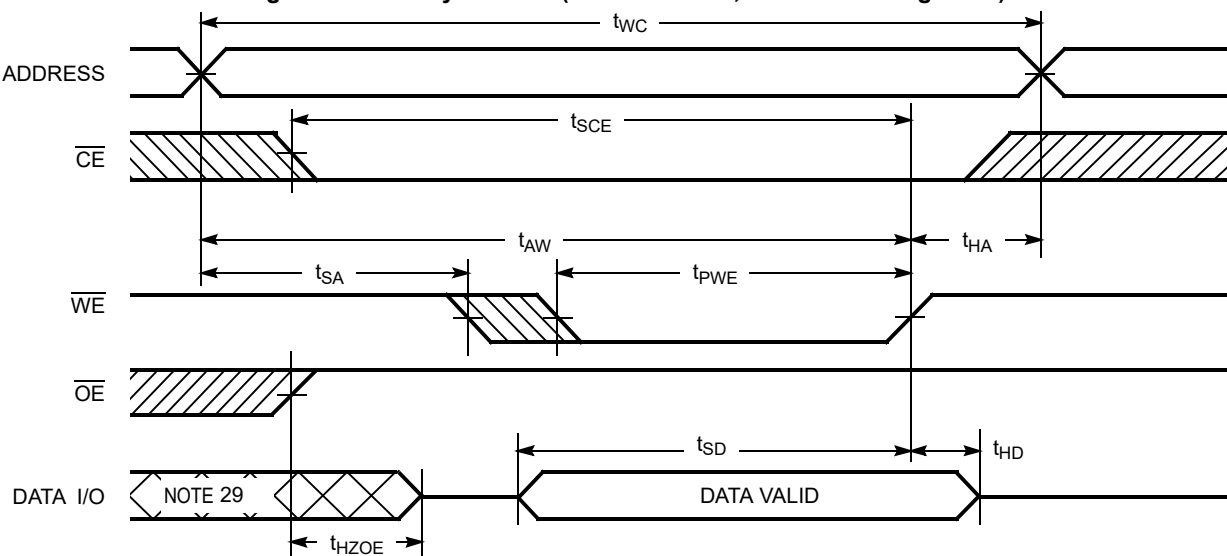


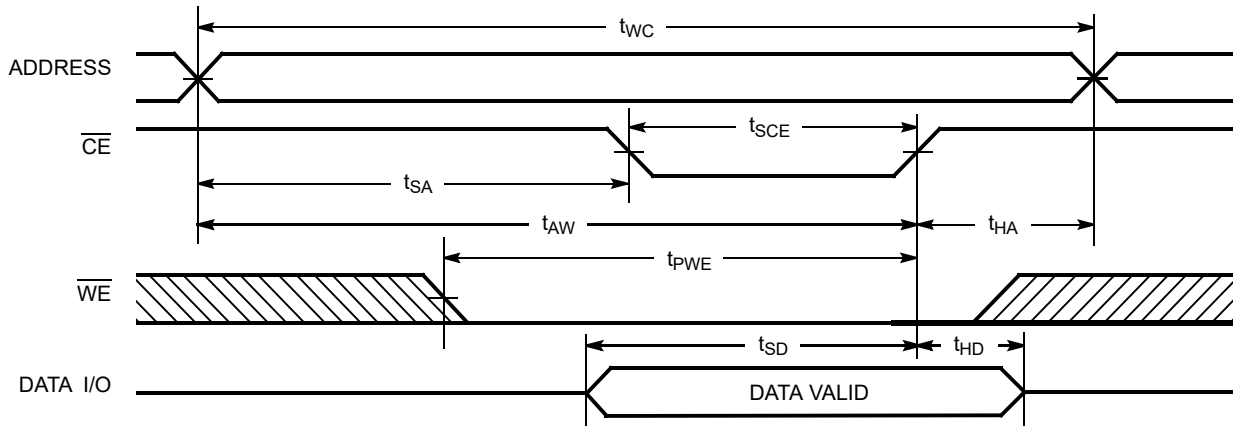
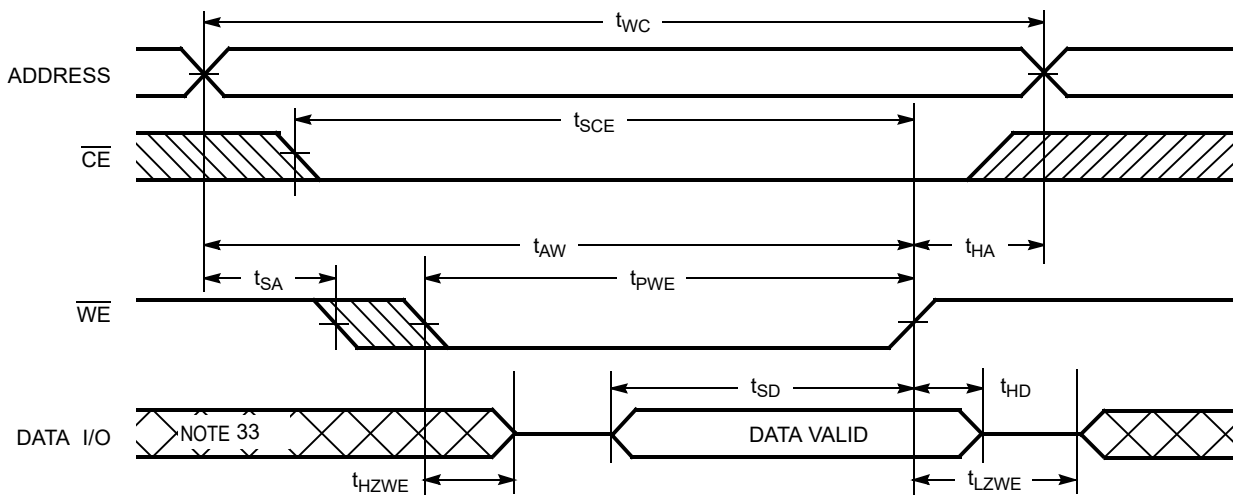
Figure 5. Write Cycle No. 1 ( $\overline{\text{WE}}$  Controlled,  $\overline{\text{OE}}$  HIGH During Write) [27, 28]



### Notes

24. Device is continuously selected.  $\overline{\text{OE}}, \overline{\text{CE}} = V_{\text{IL}}$ .
25.  $\overline{\text{WE}}$  is HIGH for read cycles.
26. Address valid before or similar to  $\overline{\text{CE}}$  transition LOW.
27. Data I/O is high impedance if  $\overline{\text{OE}} = V_{\text{IH}}$ .
28. If  $\overline{\text{CE}}$  goes HIGH simultaneously with  $\overline{\text{WE}}$  HIGH, the output remains in high impedance state.
29. During this period, the I/Os are in output state. Do not apply input signals.

## Switching Waveforms (continued)

Figure 6. Write Cycle No. 2 ( $\overline{\text{CE}}$  Controlled) [30, 31]Figure 7. Write Cycle No. 3 ( $\overline{\text{WE}}$  Controlled,  $\overline{\text{OE}}$  LOW) [31, 32]

## Notes

30. Data I/O is high impedance if  $\overline{\text{OE}} = V_{\text{IL}}$ .
31. If  $\overline{\text{CE}}$  goes HIGH simultaneously with  $\overline{\text{WE}}$  HIGH, the output remains in high impedance state.
32. The minimum write cycle pulse width should be equal to the sum of  $t_{\text{SD}}$  and  $t_{\text{HZWE}}$ .
33. During this period, the I/Os are in output state. Do not apply input signals.



## Truth Table

$\overline{\text{CE}}$ <sup>[34]</sup>	$\overline{\text{WE}}$	$\overline{\text{OE}}$	Inputs/Outputs	Mode	Power
H	X	X	High Z	Deselect/Power down	Standby ( $I_{\text{SB}}$ )
L	H	L	Data out	Read	Active ( $I_{\text{CC}}$ )
L	H	H	High Z	Output disabled	Active ( $I_{\text{CC}}$ )
L	L	X	Data in	Write	Active ( $I_{\text{CC}}$ )

### Note

34. Chip enable must be at CMOS levels (not floating). Intermediate voltage levels on this pin is not permitted.

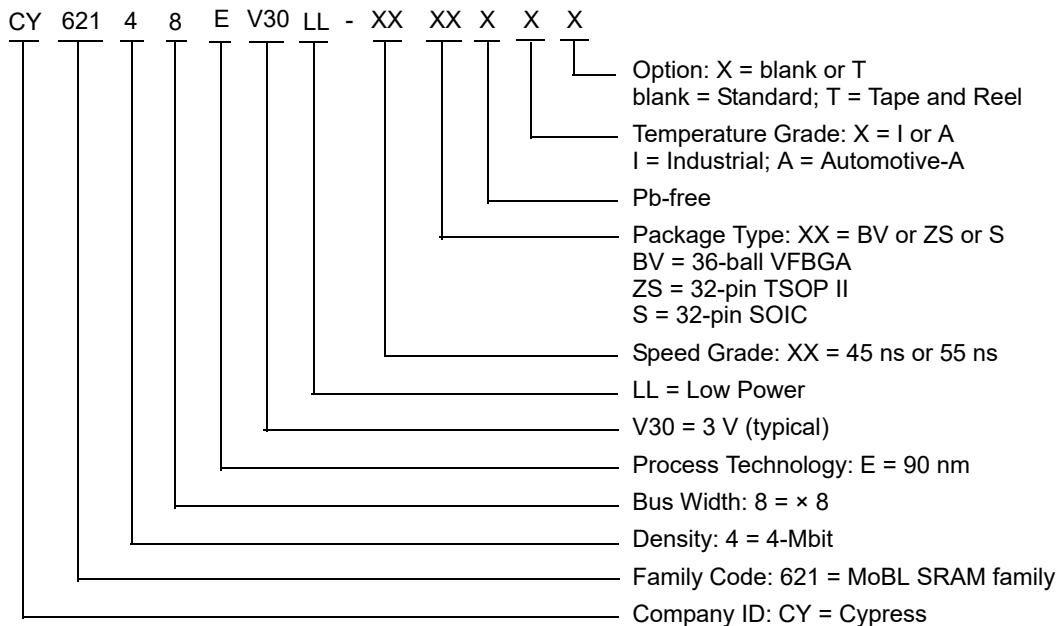


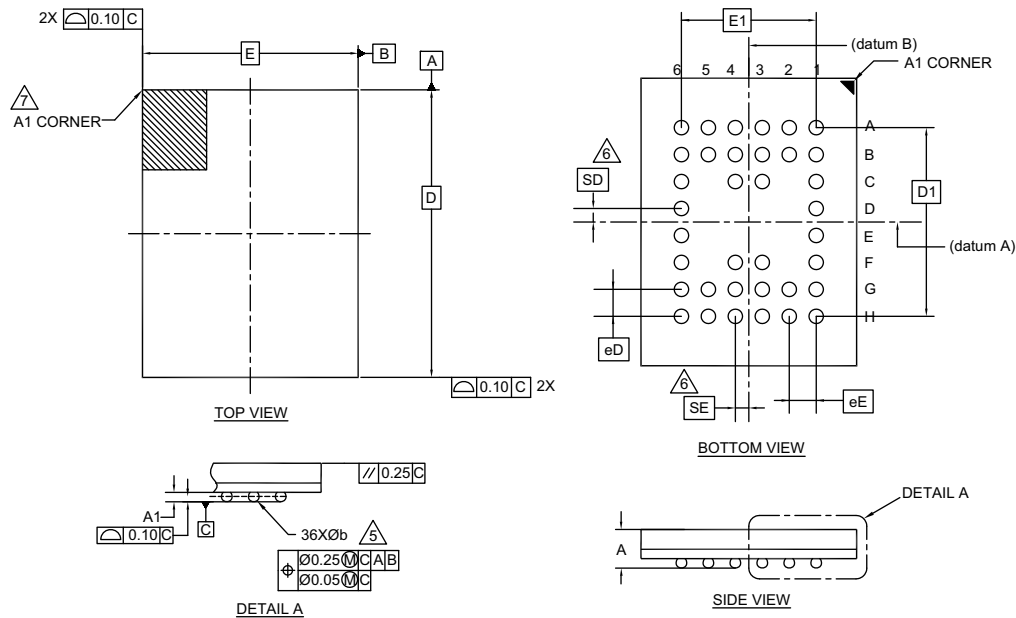
## Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62148EV30LL-45BVI	51-85149	36-ball VFBGA	Industrial
	CY62148EV30LL-45BVXI	51-85149	36-ball VFBGA (Pb-free)	
	CY62148EV30LL-45BVXIT	51-85149	36-ball VFBGA (Pb-free)	
	CY62148EV30LL-45ZSXI	51-85095	32-pin TSOP II (Pb-free)	
55	CY62148EV30LL-55SXI	51-85081	32-pin SOIC (Pb-free)	Industrial

Contact your local Cypress sales representative for availability of these parts.

## Ordering Code Definitions



**Package Diagrams****Figure 8. 36-ball VFBGA (8.0 × 6.0 × 1.0 mm) Package Outline, 51-85149**

SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	-	-	1.00
A1	0.16	-	-
D	8.00 BSC		
E	6.00 BSC		
D1	5.25 BSC		
E1	3.75 BSC		
MD	8		
ME	6		
N	36		
Ø b	0.25	0.30	0.35
eD	0.75 BSC		
eE	0.75 BSC		
SD	0.375 BSC		
SE	0.375 BSC		

**NOTES:**

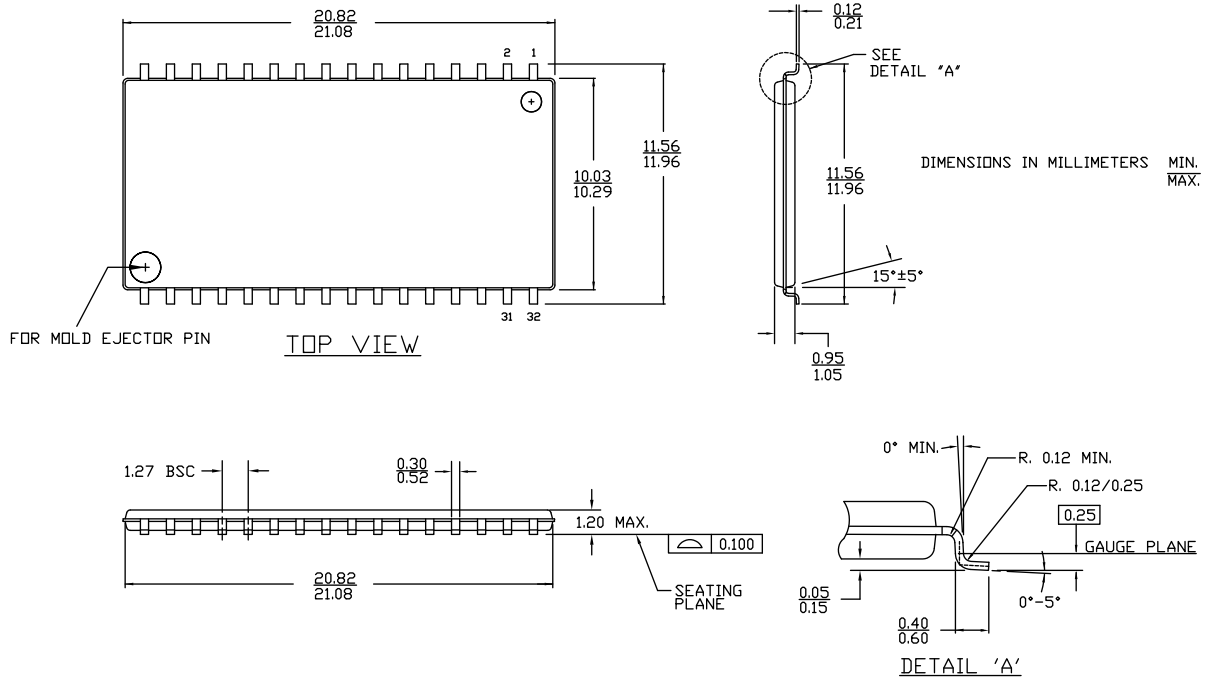
- ALL DIMENSIONS ARE IN MILLIMETERS.
  - SOLDER BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-020.
  - "e" REPRESENTS THE SOLDER BALL GRID PITCH.
  - SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION. SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION. N IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
5. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
6. "SD" AND "SE" ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW "SD" OR "SE" = 0. WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW "SD" = eD/2 AND "SE" = eE/2.
7. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK METALIZED MARK, INDENTATION OR OTHER MEANS.
8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED SOLDER BALLS.

51-85149 \*G



Package Diagrams (continued)

Figure 9. 32-pin TSOP II (20.95 × 11.76 × 1.0 mm) Package Outline, 51-85095

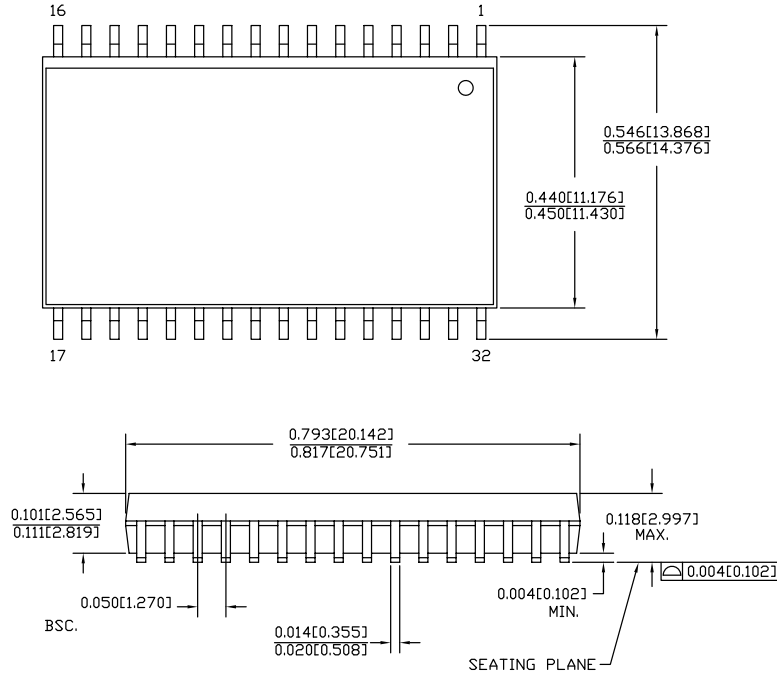


51-85095 \*D



Package Diagrams (continued)

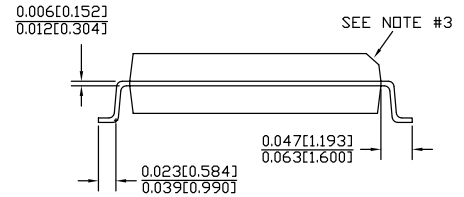
Figure 10. 32-pin SOIC (450 Mils) Package Outline, 51-85081



NOTE

1. DIMENSIONS IN INCHES[MM] MIN.  
MAX.
2. PACKAGE WEIGHT: See Cypress Package Material Declaration Datasheet (PMDD) posted on the Cypress web.
3. The chamfer feature is optional. If it is not present, then Pin 1 identifier must be located within the index area indicated.

PART #	
S32.45	STANDARD PKG.
SZ32.45	LEAD FREE PKG.



51-85081 \*F



## Acronyms

Acronym	Description
$\overline{\text{BHE}}$	Byte High Enable
$\overline{\text{BLE}}$	Byte Low Enable
CMOS	Complementary Metal Oxide Semiconductor
$\overline{\text{CE}}$	Chip Enable
I/O	Input/Output
$\overline{\text{OE}}$	Output Enable
SRAM	Static Random Access Memory
TSOP	Thin Small Outline Package
VFBGA	Very Fine-Pitch Ball Grid Array
$\overline{\text{WE}}$	Write Enable

## Document Conventions

### Units of Measure

Symbol	Unit of Measure
$^{\circ}\text{C}$	degree Celsius
$\mu\text{A}$	microampere
mA	milliampere
ns	nanosecond
pF	picofarad
V	volt
W	watt



## Document History Page

Document Title: CY62148EV30 MoBL, 4-Mbit (512K × 8) Static RAM			
Document Number: 38-05576			
Region	ECN	Submission Date	Description of Change
**	223225	05/05/2004	New data sheet.
*A	247373	07/28/2004	<p>Changed status from Advance Information to Preliminary.</p> <p>Updated <a href="#">Operating Range</a>:</p> <p>Updated Note 7 (Changed <math>V_{CC}</math> stabilization time from 100 <math>\mu</math>s to 200 <math>\mu</math>s).</p> <p>Updated <a href="#">Data Retention Characteristics</a>:</p> <p>Changed maximum value of <math>I_{CCDR}</math> parameter from 2.0 <math>\mu</math>A to 2.5 <math>\mu</math>A.</p> <p>Changed minimum value of <math>t_R</math> parameter from 100 <math>\mu</math>s to <math>t_{RC}</math> ns.</p> <p>Updated <a href="#">Switching Characteristics</a>:</p> <p>Changed minimum value of <math>t_{OHA}</math> parameter from 6 ns to 10 ns corresponding to both 35 ns and 45 ns speed bins.</p> <p>Changed maximum value of <math>t_{DOE}</math> parameter from 15 ns to 18 ns corresponding to 35 ns speed bin.</p> <p>Changed maximum value of <math>t_{HZOE}</math>, <math>t_{HZWE}</math> parameters from 12 ns to 15 ns corresponding to 35 ns speed bin and 15 ns to 18 ns corresponding to 45 ns speed bin.</p> <p>Changed minimum value of <math>t_{SCE}</math> parameter from 25 ns to 30 ns corresponding to 35 ns speed bin and 40 ns to 35 ns corresponding to 45 ns speed bin.</p> <p>Changed maximum value of <math>t_{HZCE}</math> parameter from 12 ns to 18 ns corresponding to 35 ns speed bin and 15 ns to 22 ns corresponding to 45 ns speed bin.</p> <p>Changed minimum value of <math>t_{SD}</math> parameter from 15 ns to 18 ns corresponding to 35 ns speed bin and 20 ns to 22 ns corresponding to 45 ns speed bin.</p> <p>Updated <a href="#">Ordering Information</a>:</p> <p>Updated part numbers.</p>
*B	414807	12/16/2005	<p>Changed status from Preliminary to Final.</p> <p>Changed the address of Cypress Semiconductor Corporation on page 1 from "3901 North First Street" to "198 Champion Court".</p> <p>Updated <a href="#">Features</a>:</p> <p>Removed 35 ns speed bin related information.</p> <p>Updated <a href="#">Pin Configurations</a>:</p> <p>Changed ball C3 from DNU to NC.</p> <p>Removed the Note "DNU pins have to be left floating or tied to <math>V_{SS}</math> to ensure proper application." and its reference.</p> <p>Added 32-pin SOIC pinout.</p> <p>Updated <a href="#">Electrical Characteristics</a>:</p> <p>Removed "L" version of CY62148EV30.</p> <p>Changed typical value of <math>I_{CC}</math> parameter from 12 mA to 15 mA corresponding to Test Condition "f = <math>f_{max}</math>".</p> <p>Changed typical value of <math>I_{CC}</math> parameter from 1.5 mA to 2 mA corresponding to Test Condition "f = 1 MHz".</p> <p>Changed maximum value of <math>I_{CC}</math> parameter from 2 mA to 2.5 mA corresponding to Test Condition "f = 1 MHz".</p> <p>Changed typical value of <math>I_{SB1}</math> and <math>I_{SB2}</math> parameters from 0.7 <math>\mu</math>A to 1 <math>\mu</math>A.</p> <p>Changed maximum value of <math>I_{SB1}</math> and <math>I_{SB2}</math> parameters from 2.5 <math>\mu</math>A to 7 <math>\mu</math>A.</p> <p>Updated <a href="#">AC Test Loads and Waveforms</a>:</p> <p>Changed the AC test load capacitance value from 50 pF to 30 pF.</p> <p>Updated <a href="#">Data Retention Characteristics</a>:</p> <p>Changed maximum value of <math>I_{CCDR}</math> parameter from 2.5 <math>\mu</math>A to 7 <math>\mu</math>A.</p> <p>Added typical value of <math>I_{CCDR}</math> parameter.</p> <p>Updated <a href="#">Switching Characteristics</a>:</p> <p>Changed minimum value of <math>t_{LZOE}</math> parameter from 3 ns to 5 ns.</p> <p>Changed minimum value of <math>t_{LZCE}</math> and <math>t_{LZWE}</math> parameters from 6 ns to 10 ns.</p> <p>Changed maximum value of <math>t_{HZCE}</math> parameter from 22 ns to 18 ns.</p> <p>Changed minimum value of <math>t_{PWE}</math> parameter from 30 ns to 35 ns.</p> <p>Changed minimum value of <math>t_{SD}</math> parameter from 22 ns to 25 ns.</p>



## Document History Page (continued)

Document Title: CY62148EV30 MoBL, 4-Mbit (512K × 8) Static RAM			
Document Number: 38-05576			
Region	ECN	Submission Date	Description of Change
*B (cont.)	414807	12/16/2005	Updated <a href="#">Ordering Information</a> : Updated part numbers. Removed "Package Name" column. Added "Package Diagram" column. Updated <a href="#">Package Diagrams</a> : spec 51-85149 – Changed revision from *B to *C. Added spec 51-85081 *B. Updated to new template.
*C	464503	05/25/2006	Added Automotive Temperature Range related information in all instances across the document. Updated <a href="#">Ordering Information</a> : Updated part numbers.
*D	833080	03/09/2007	Updated <a href="#">Electrical Characteristics</a> : Added details of $V_{IL}$ parameter corresponding to Test Condition "SOIC package". Added Note 10 and referred the same note in the maximum value of $V_{IL}$ parameter corresponding to SOIC package.
*E	890962	03/30/2007	Removed Automotive Temperature Range related information in all instances across the document. Updated <a href="#">Features</a> : Added Note 1 and referred the same note in 32-pin SOIC package. Updated <a href="#">Electrical Characteristics</a> : Added Note 11 and referred the same note in $I_{SB2}$ parameter. Updated <a href="#">Switching Characteristics</a> : Added values for all parameters corresponding to 55 ns Industrial Temperature Range. Updated <a href="#">Ordering Information</a> : Updated part numbers.
*F	987940	04/18/2007	Updated <a href="#">Electrical Characteristics</a> : Changed maximum value of $V_{OL}$ parameter from 0.4 V to 0.2 V corresponding to Industrial Temperature Range at $I_{OL} = 0.1$ mA. Changed maximum value of $V_{IL}$ parameter from 0.6 V to 0.4 V corresponding to Industrial Temperature Range, SOIC package at $V_{CC} = 2.2$ V to 2.7 V. Updated Note 10. Updated Note 11 (made the note applicable for both $I_{SB2}$ and $I_{CCDR}$ parameters).
*G	2548575	08/05/2008	Added Automotive-A Temperature Range related information in all instances across the document. Updated <a href="#">Ordering Information</a> : Updated part numbers. Updated to new template.
*H	2769239	09/25/2009	Updated <a href="#">Ordering Information</a> : Updated part numbers.
*I	2944332	06/04/2010	Updated <a href="#">Truth Table</a> : Added Note 34 and referred the same note in " $\overline{CE}$ " column. Updated <a href="#">Package Diagrams</a> : spec 51-85149 – Changed revision from *C to *D. spec 51-85095 – Changed revision from ** to *A. spec 51-85081 – Changed revision from *B to *C.
*J	3007403	08/13/2010	Updated <a href="#">Ordering Information</a> : No change in part numbers. Added <a href="#">Ordering Code Definitions</a> . Updated to new template. Completing Sunset Review.

## Document History Page (continued)

Document Title: CY62148EV30 MoBL, 4-Mbit (512K × 8) Static RAM			
Document Number: 38-05576			
Region	ECN	Submission Date	Description of Change
*K	3110202	12/14/2010	Updated <a href="#">Logic Block Diagram</a> . Updated <a href="#">Ordering Information</a> : No change in part numbers. Updated <a href="#">Ordering Code Definitions</a> .
*L	3302901	07/06/2011	Updated <a href="#">Functional Description</a> : Removed "For best practice recommendations, refer to the Cypress application note <a href="#">AN1064, SRAM System Guidelines</a> ." at the end. Updated <a href="#">Ordering Information</a> : No change in part numbers. Updated <a href="#">Ordering Code Definitions</a> . Updated <a href="#">Package Diagrams</a> : spec 51-85095 – Changed revision from *A to *B. Updated to new template. Completing Sunset Review.
*M	3363097	09/07/2011	Updated <a href="#">Data Retention Characteristics</a> : Removed reference of Note 12 in I <sub>CCDR</sub> parameter. Added Note 14 and referred the same note in I <sub>CCDR</sub> parameter. Updated <a href="#">Package Diagrams</a> : spec 51-85149 – Changed revision from *D to *E. spec 51-85081 – Changed revision from *C to *D.
*N	3546715	03/09/2012	Updated <a href="#">Electrical Characteristics</a> : Updated Note 10 (Removed the line "Refer to <a href="#">AN13470</a> for details").
*O	3733339	09/04/2012	Minor text edits. Completing Sunset Review.
*P	4102967	08/23/2013	Updated <a href="#">Switching Characteristics</a> : Added Note 17 and referred the same note in "Parameter" column. Updated <a href="#">Package Diagrams</a> : spec 51-85081 – Changed revision from *D to *E. Updated to new template. Completing Sunset Review.
*Q	4307881	04/09/2014	Updated <a href="#">Switching Characteristics</a> : Updated description of t <sub>PD</sub> parameter (Replaced "CE HIGH to power-up" with "CE HIGH to power-down").
*R	4576526	11/21/2014	Updated <a href="#">Functional Description</a> : Added "For a complete list of related 1documentation, <a href="#">click here</a> ." at the end. Updated <a href="#">Switching Characteristics</a> : Added Note 23 and referred the same note in "Write Cycle". Updated <a href="#">Switching Waveforms</a> : Added Note 32 and referred the same note in <a href="#">Figure 7</a> .
*S	4802206	06/18/2015	Updated <a href="#">Package Diagrams</a> : spec 51-85149 – Changed revision from *E to *F. spec 51-85095 – Changed revision from *B to *D. Updated to new template.
*T	5234869	04/22/2016	Updated <a href="#">Ordering Information</a> : Updated part numbers. Updated <a href="#">Ordering Code Definitions</a> (Added Tape and Reel option). Updated <a href="#">Package Diagrams</a> : spec 51-85149 – Changed revision from *F to *G. Updated to new template.



## Document History Page (continued)

Document Title: CY62148EV30 MoBL, 4-Mbit (512K × 8) Static RAM			
Document Number: 38-05576			
Region	ECN	Submission Date	Description of Change
*U	5480386	10/18/2016	Updated <a href="#">Thermal Resistance</a> : Replaced “two-layer” with “four-layer” in “Test Conditions” column. Updated values of $\Theta_{JA}$ parameter and $\Theta_{JC}$ parameter corresponding to all packages. Updated to new template. Completing Sunset Review.
*V	6045156	01/25/2018	Updated <a href="#">Ordering Information</a> : Updated part numbers. Updated to new template.
*W	6531864	04/03/2019	Updated to new template.
*X	6906316	06/26/2020	Updated <a href="#">Features</a> : Changed value of Typical standby current from 1 $\mu$ A to 2.5 $\mu$ A. Changed value of Typical active current from 2 mA to 3.5 mA. Updated <a href="#">Product Portfolio</a> : Changed typical value of Operating $I_{CC}$ from 2 mA to 3.5 mA corresponding to all packages and “f = 1 MHz”. Changed maximum value of Operating $I_{CC}$ from 2.5 mA to 6 mA corresponding to all packages and “f = 1 MHz”. Changed typical value of Standby, $I_{SB2}$ from 1 $\mu$ A to 2.5 $\mu$ A corresponding to all packages. Updated <a href="#">Electrical Characteristics</a> : Changed typical value of $I_{CC}$ parameter from 2 mA to 3.5 mA corresponding to all speed bins and Test Condition “f = 1 MHz”. Changed maximum value of $I_{CC}$ parameter from 2.5 mA to 6 mA corresponding to all speed bins and Test Condition “f = 1 MHz”. Changed typical value of $I_{SB1}$ parameter from 1 $\mu$ A to 2.5 $\mu$ A corresponding to all speed bins. Changed typical value of $I_{SB2}$ parameter from 1 $\mu$ A to 2.5 $\mu$ A corresponding to all speed bins. Updated <a href="#">Data Retention Characteristics</a> : Changed typical value of $I_{CCDR}$ parameter from 0.8 $\mu$ A to 3 $\mu$ A. Changed maximum value of $I_{CCDR}$ parameter from 7 $\mu$ A to 8.8 $\mu$ A. Updated <a href="#">Package Diagrams</a> : spec 51-85081 – Changed revision from *E to *F. Updated to new template.



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